

Complementary power Darlingtons

**Features**

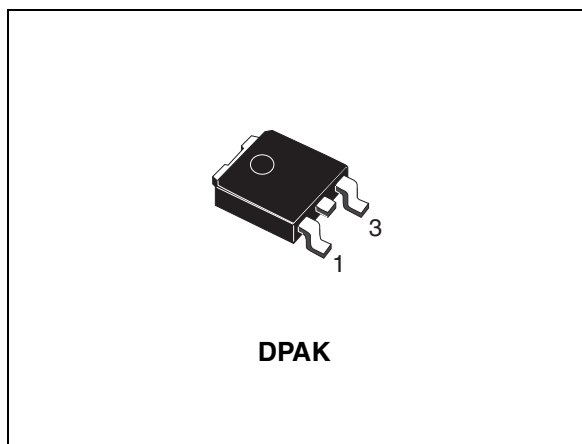
- Low collector-emitter saturation voltage
- Integrated antiparallel collector-emitter diode

**Applications**

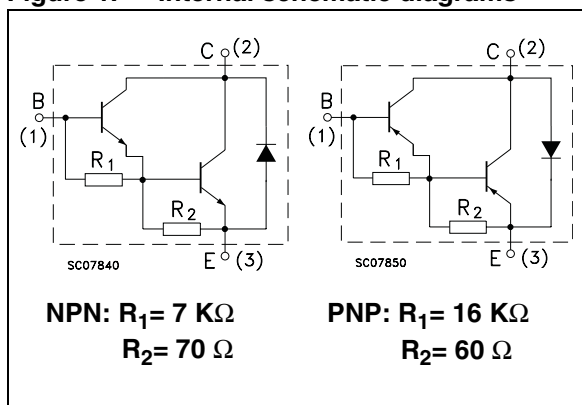
- General purpose linear and switching

**Description**

The devices are manufactured in planar technology with “base island” layout and monolithic Darlingtons configuration. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.



**Figure 1. Internal schematic diagrams**



**Table 1. Device summary**

Order codes	Marking	Polarity	Package	Packaging
MJD122T4	MJD122	NPN	DPAK	Tape and reel
MJD127T4	MJD127	PNP		

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	100	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	100	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	5	V
$I_C$	Collector current	8	A
$I_{CM}$	Collector peak current	16	A
$I_B$	Base current	0.12	A
$P_{TOT}$	Total dissipation at $T_{case} = 25^\circ\text{C}$	20	W
$T_{stg}$	Storage temperature	-65 to 150	$^\circ\text{C}$
$T_J$	Max. operating junction temperature	150	$^\circ\text{C}$

Note: For PNP types voltage and current values are negative.

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-c}$	Thermal resistance junction-case max.	6.25	$^\circ\text{C}/\text{W}$

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ °C}$ ; unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = 100\text{ V}$		-	10	$\mu\text{A}$
$I_{\text{CEO}}$	Collector cut-off current ( $I_{\text{B}} = 0$ )	$V_{\text{CE}} = 50\text{ V}$		-	10	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = 5\text{ V}$		-	2	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = 30\text{ mA}$	100	-		V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 4\text{ A}$ $I_{\text{B}} = 16\text{ mA}$ $I_{\text{C}} = 8\text{ A}$ $I_{\text{B}} = 80\text{ mA}$		-	2 4	V V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 8\text{ A}$ $I_{\text{B}} = 80\text{ mA}$		-	4.5	V
$V_{\text{BE(on)}}^{(1)}$	Base-emitter on voltage	$I_{\text{C}} = 4\text{ A}$ $V_{\text{CE}} = 4\text{ V}$		-	2.8	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 4\text{ A}$ $V_{\text{CE}} = 4\text{ V}$ $I_{\text{C}} = 8\text{ A}$ $V_{\text{CE}} = 4\text{ V}$	1000 100	-	12000	

1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$

**Note:** For PNP types voltage and current values are negative.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

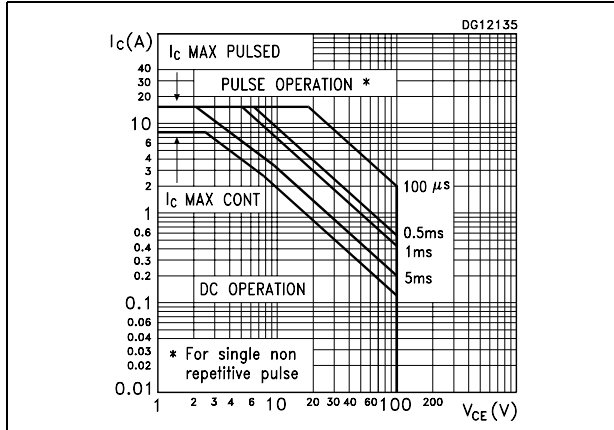


Figure 3. Derating curve



Figure 4. DC current gain for NPN type



Figure 5. DC current gain for PNP type



Figure 6. Collector-emitter saturation voltage for NPN type

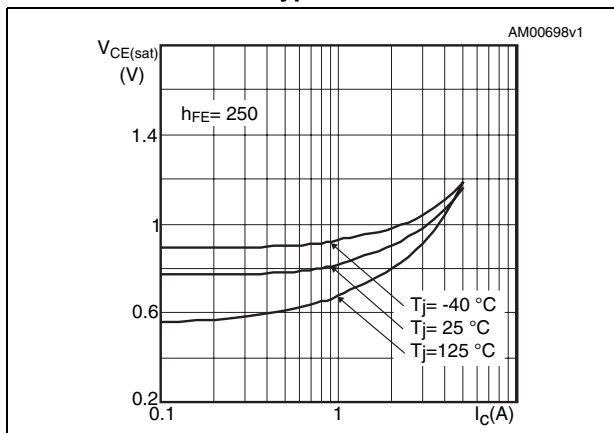


Figure 7. Collector-emitter saturation voltage for PNP type

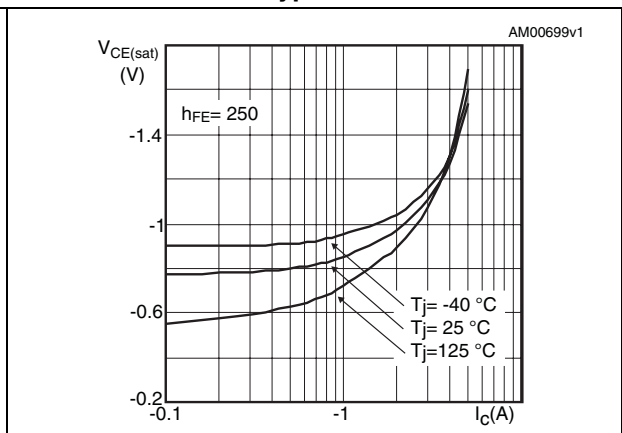


Figure 8. Base-emitter saturation voltage for NPN type



Figure 9. Base-emitter saturation voltage for PNP type



Figure 10. Base-emitter on voltage for NPN type



Figure 11. Base-emitter on voltage for PNP type



Figure 12. Resistive load switching times for NPN type (on)



Figure 13. Resistive load switching times for PNP type (on)



Figure 14. Resistive load switching times for NPN type (off)



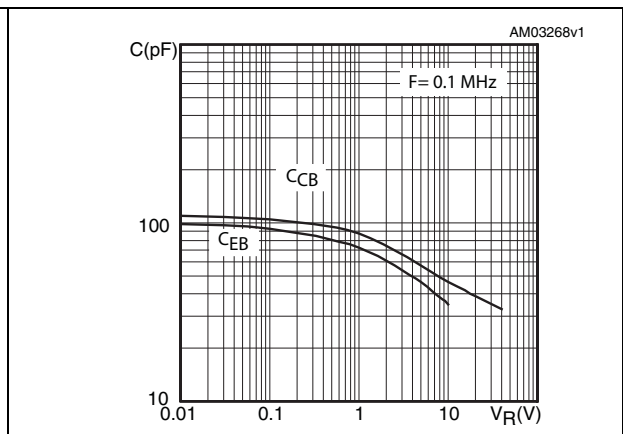
Figure 15. Resistive load switching times for PNP type (off)



Figure 16. Capacitances for NPN type



Figure 17. Capacitances for PNP type



### 3 Test circuits

**Figure 18. Resistive load switching for NPN type**



- 1. Fast electronic switch
- 2. Non-inductive resistor

**Figure 19. Resistive load switching for PNP type**



- 1. Fast electronic switch
- 2. Non-inductive resistor



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**TO-252 (DPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



## 5 Revision history

**Table 5. Document revision history**

Date	Revision	Changes
01-Aug-2002	8	
01-Oct-2007	9	Collector current limits have been improved
03-Oct-2007	10	Package mechanical data updated
21-Apr-2009	11	The device MJD127 has been inserted <a href="#">Section 2.1: Electrical characteristics (curves)</a> has been updated

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